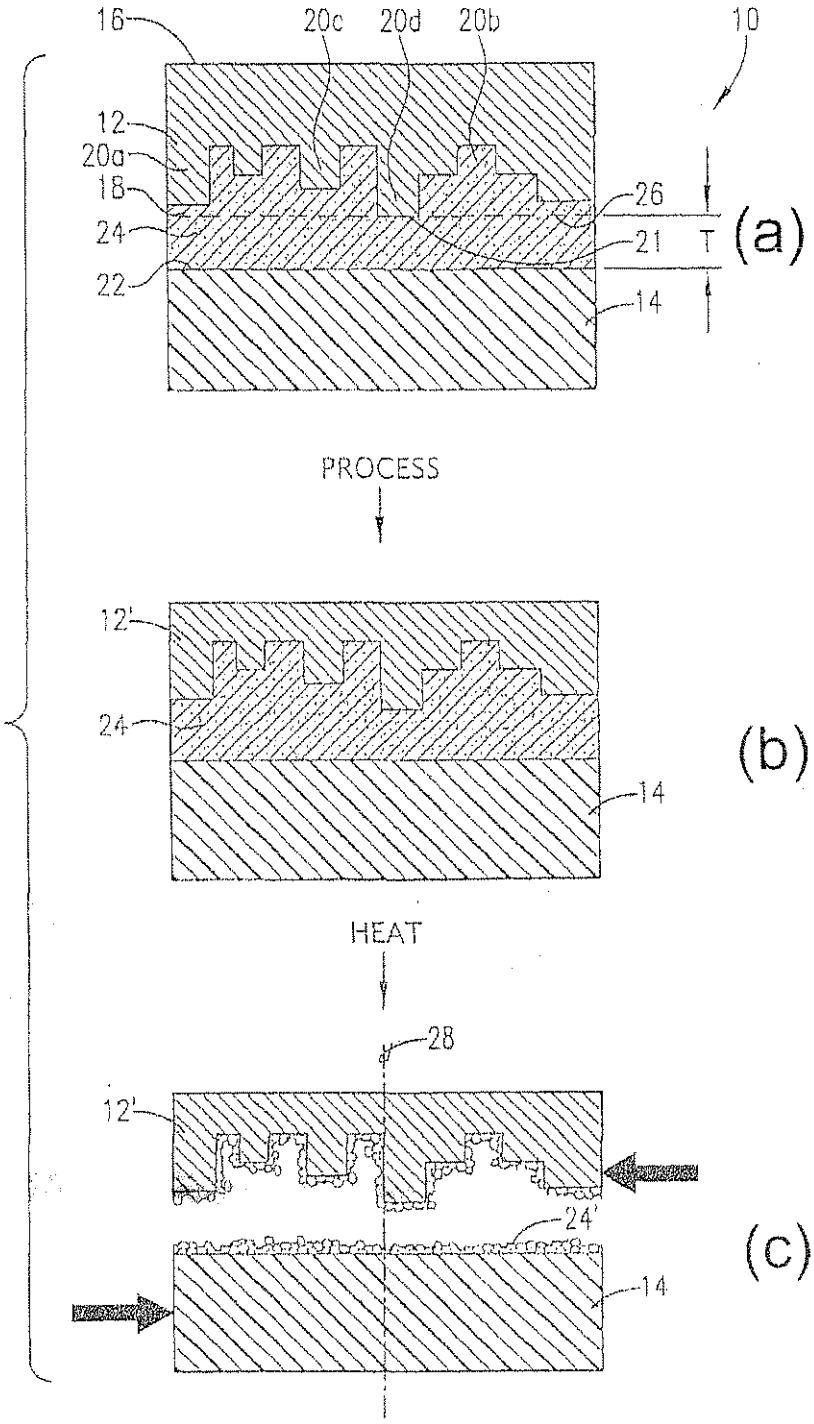

16
20c
20d
20b
10
12
20a
18
24
22
26
21
T
14
(a)
PROCESS
12'
24
14
(b)
HEAT
28
12'
24'
14
(c)

Fig. 1

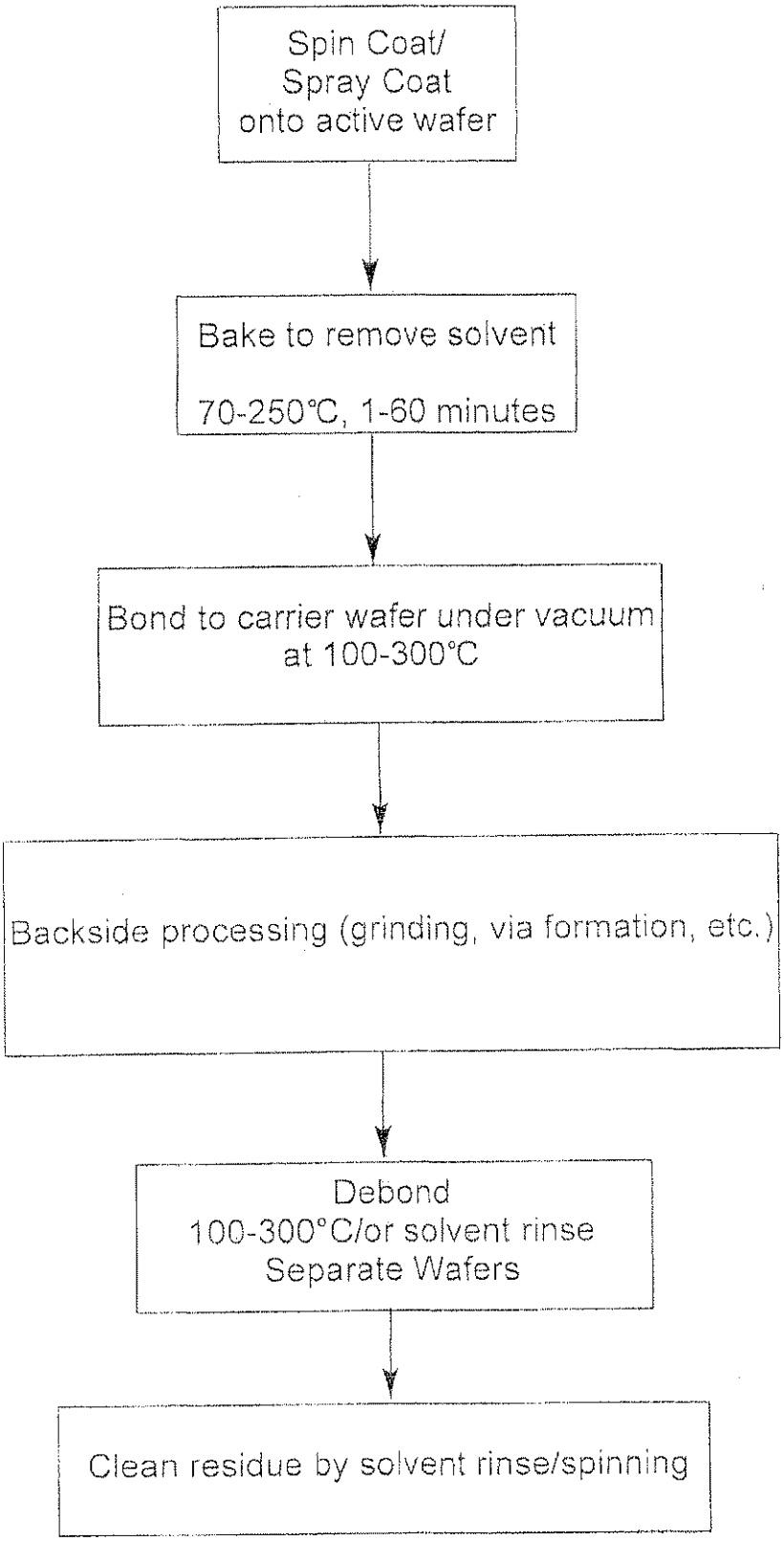

Spin Coat/
Spray Coat
onto active wafer
Bake to remove solvent
70-250°C, 1-60 minutes
Bond to carrier wafer under vacuum
at 100-300°C
Backside processing (grinding, via formation, etc.)
Debond
100-300°C/or solvent rinse
Separate Wafers
Clean residue by solvent rinse/spinning

Fig. 2

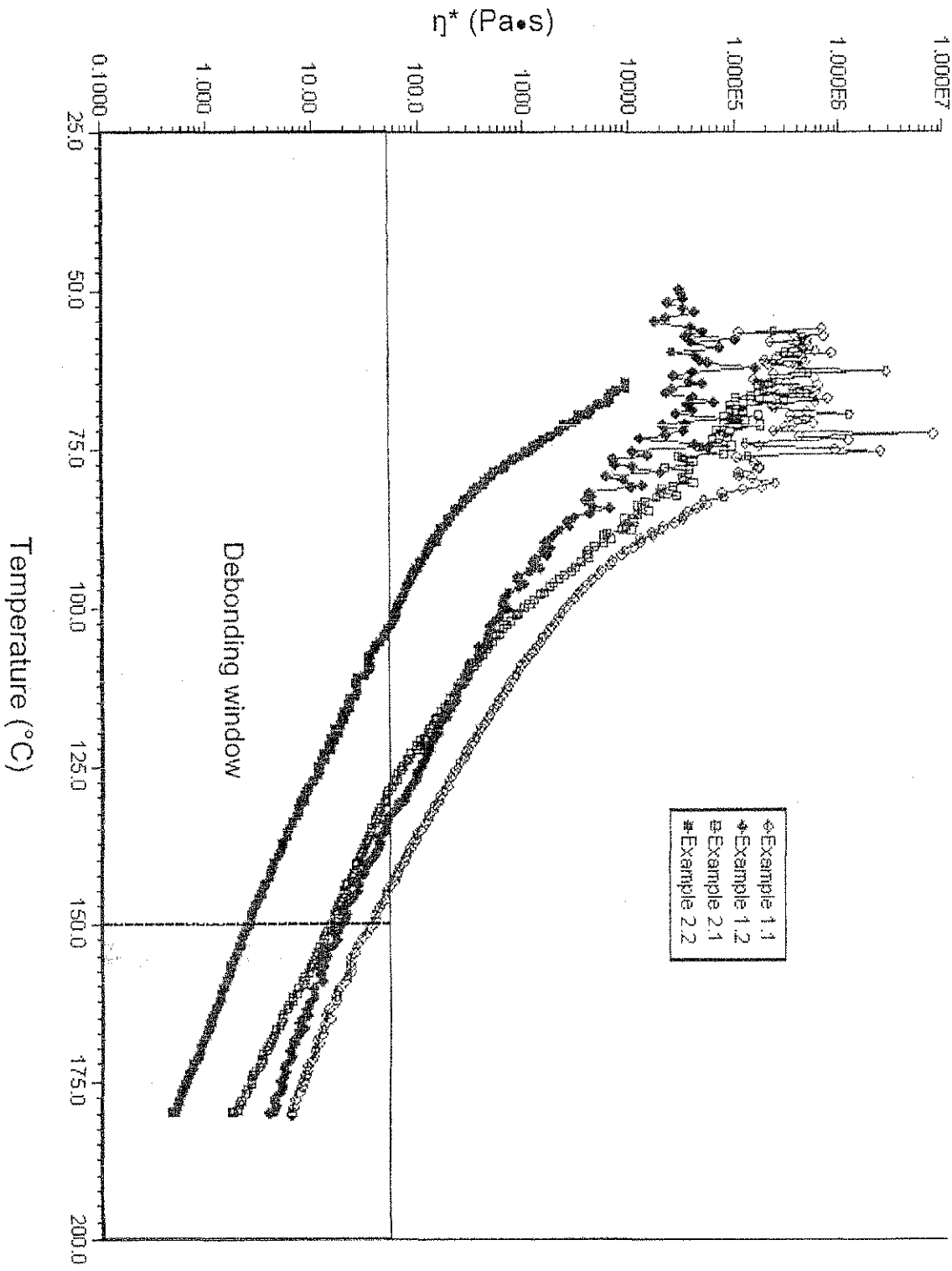

η* (Pa•s)
1.000E7
1.000E6
1.000E5
10000
1000
100.0
10.00
1.000
0.1000
25.0
50.0
75.0
100.0
125.0
150.0
175.0
200.0
Temperature (°C)
Debonding window
Example 1.1
Example 1.2
Example 2.1
Example 2.2

Fig. 3

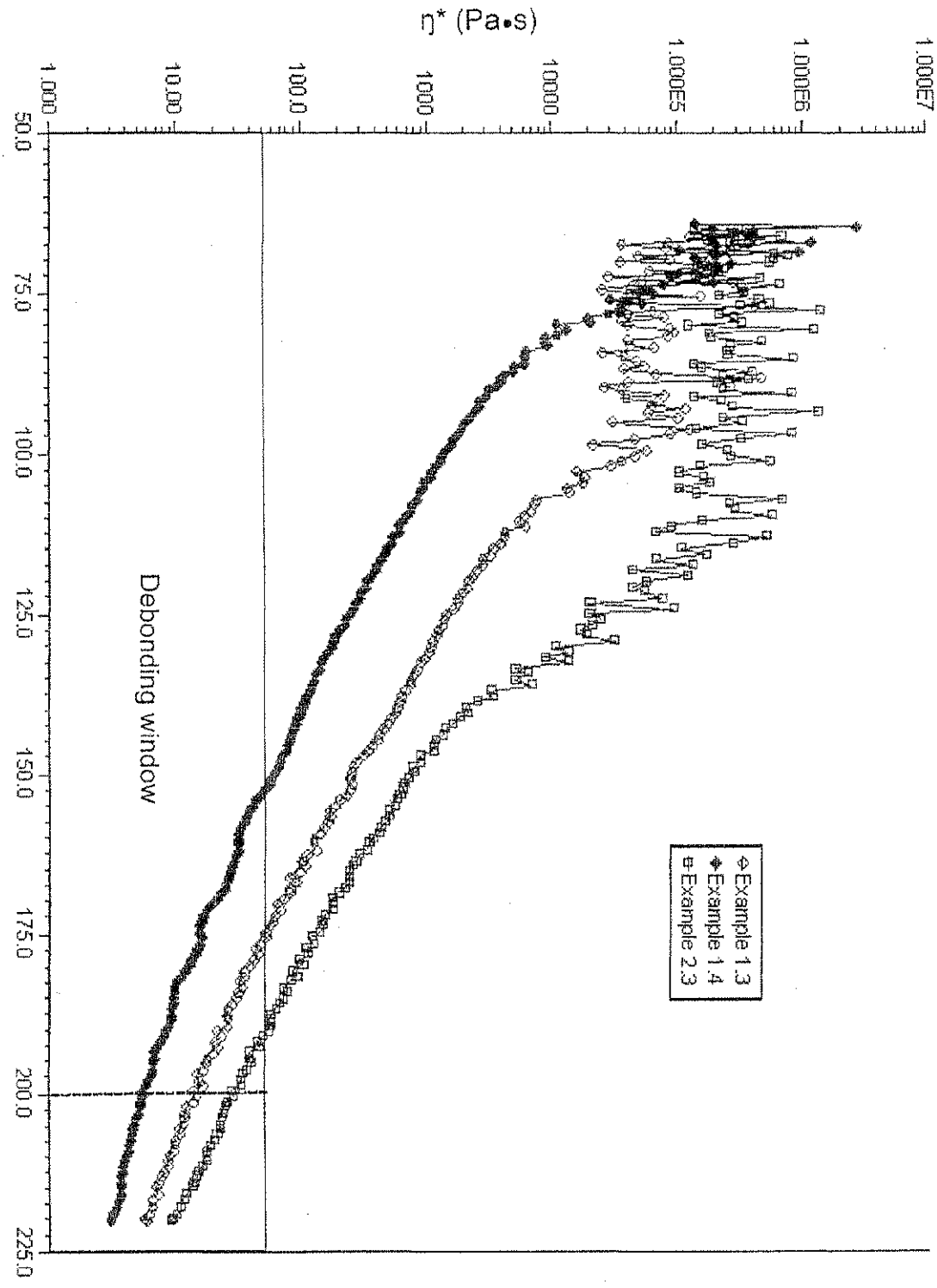

η* (Pa•s)
1.000E7
1.000E6
1.000E5
10000
1000
100.0
10.00
1.000
50.0
75.0
100.0
125.0
150.0
175.0
200.0
225.0
Temperature (°C)
Debonding window
Example 1.3
Example 1.4
Example 2.3

Fig. 4

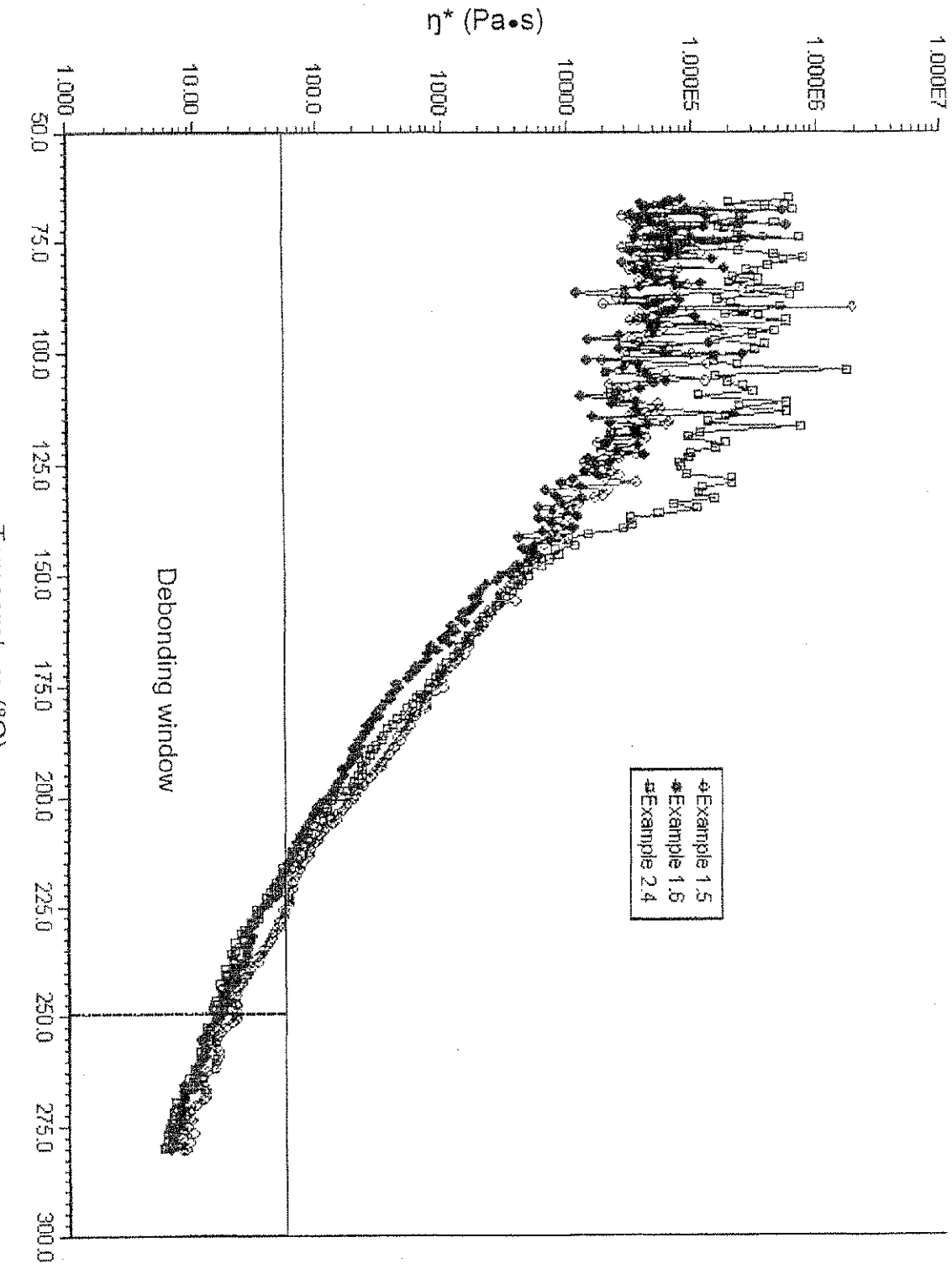

η* (Pa•s)
1.000E7
1.000E6
1.000E5
10000
1000
100.0
10.00
1.000
50.0
75.0
100.0
125.0
150.0
175.0
200.0
225.0
250.0
275.0
300.0
Temperature (°C)
Debonding window
Example 1.5
Example 1.6
Example 2.4

Fig. 5